



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/774,515
				Filing Date	February 10, 2004
				First Named Inventor	John T. Moore, et al.
				Art Unit	2845 2813
				Examiner Name	Not Yet Assigned
Sheet	1	of	3	Attorney Docket Number	M4065.0697//P697-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
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	L	US 4,267,261	5/1981	Hallman et al.	
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	N	US 4,608,296	8/1986	Keem et al.	
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	R	US 4,668,968	5/1987	Ovshinsky et al.	
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	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
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U1	US 5,534,711	7/1996	Ovshinsky et al.	
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M3	US 6,605,527	8/2003	Dennison et al.	
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Q3	US 6,642,102	11/2003	Xu	
R3	US 6,646,297	11/2003	Dennison	

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				Art Unit	28452813
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S3	US 6,649,928	11/2003	Dennison	
T3	US 6,667,900	12/2003	Lowery et al.	
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Y3	US 6,687,427	2/2004	Ramalingam et al.	
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A4	US 6,696,355	2/2004	Dennison	
B4	US 6,687,153	2/2004	Lowery	
C4	US 6,707,712	3/2004	Lowery	
D4	US 6,714,954	3/2004	Ovshinsky et al.	

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NON PATENT LITERATURE DOCUMENTS				
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Glenn M. Moore 12/8/04

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				Art Unit	Not Yet Assigned 2813
				Examiner Name	Not Yet Assigned
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U.S. PATENT DOCUMENTS					
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JMB	AA	6,388,324	05/14/2002	Kozicki et al. **	
	AB	US 2002/0000666	01/03/2002	Kozicki et al. **	
	AC	5,500,532	03/19/1996	Kozicki et al. **	
	AD	US 2002/0168820	11/14/2002	Kozicki et al. **	
	AE	6,469,364	10/22/2002	Kozicki **	
	AF	US-2003/0137896-A1	07-24-2003	Kozicki **	
	AG	6,473,332	10/2002	Ignatiev et al. **	
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	AN	2003/0027416 APP	2/6/2003	Moore **	
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	AR	2002/0163828 APP	11/2002	Krieger et al. **	
	AS	6,072,716	6/2000	Jacobson et al. **	
	AT	5,272,359	12/93	Nagasubramanian et al. **	
	AU	4,671,618	6/87	Wu et al. **	
	AV	4,800,526	1/89	Lewis **	
	AW	2003/0035314	02/20/03	Kozicki **	
JMB	AX	2003/0035315	02/20/03	Kozicki **	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
<i>JMB</i>	BA	WO 97/48032		12/18/1997	Kozicki et al. **		
<i>JMB</i>	BB	WO 99/28914		06/10/1999	Kozicki et al. **		
	BC						
	BD						

Examiner Signature	<i>[Signature]</i>	Date Considered	12/8/04
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.






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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>MS</i>	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃ Te ₅ chalcogenide glass, Vacuum 59 (2000) 845-853. **	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189. **	
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	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171. **	
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	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104. **	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810. **	
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	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420. **	
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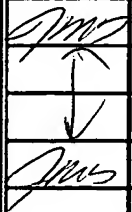
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Examiner Signature	<i>George M. M.</i>	Date Considered	12/8/04
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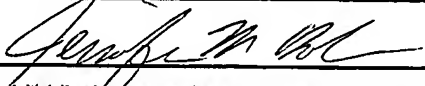
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U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	AA	09/779,963	Moore * *			02/08/01	
	AB	09/843,100	Campbell, et al. * *			08/29/01	
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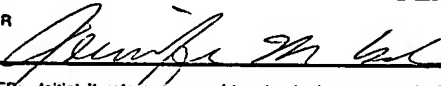
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	AS	Mirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As ₂ S ₃ films", Journal of Applied Physics, Vol. 47, No. 6, June, 1978, pps. 2767-2772. * *	
	AT	Kawaguchi, et al., "Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems", Journal of Applied Physics, 79, June 1996, pps. 9096-9104. * *	

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT John T. Moore et al.			
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U.S. PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
JMS	AR		Kluger, et al., "Silver photodiffusion in amorphous Ge ₂ Se ₁₀ ", Journal of Non-Crystalline Solids 124 (1990) pps. 186-193. * *					
JMS	AS		Kolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advances in Physics, 1991, Vol. 40, No. 5, pps. 625-684. * *					
JMS	AT		Mitkova, et al., "Dual Chemical Role of Ag as an Additive in Chalcogenide Glasses", Physical Review Letters, Vol. 83, No. 10, pps. 3848-3851. * *					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		Mitova, "Insulating and Semiconducting Glasses", Editor: P. Sookchand, World Scientific, New Jersey, 2000, pp. 813-843. * *				
	AB						
	AT						
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		APPLICANT John T. Moore et al.			
		FILING DATE Filed Herewith		GROUP Unknown	

U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	AA	09/732,965	Gilton (as Filed) * *			12/08/2000	
	AB	5,238,862	08/24/93	Bislock et al. * *	437	52	
	AC	5,360,981	11/01/94	Owen et al. * *	257	4	
	AD	5,761,115	06/02/98	Kozicki et al. * *	365	162	
	AE	5,890,312	04/20/99	Kozicki et al. * *	365	153	
	AF	5,914,893	06/22/99	Kozicki et al. * *	365	107	
	AG	6,864,796	07/04/00	Kozicki et al. * *	365	153	
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)			
	AR		Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell (PMC). * *
			(pre-July 7, 2000) pp. 1-5.
	AS		Shimakawa et al., Photoinduced effects and metastability in amorphous semiconductors and insulators. * *
			44 ADVANCES IN PHYSICS No. 6, 475-588 (Taylor & Francis Ltd. 1995)
	AT		

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: John T. Moor et al.			
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U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
JMS ↑	AA	09/921,518	Moore (as filed and as amended) * *			08/01/2001	
	AB	10/061,825	Gilton et al. (as filed) * *			01/31/2002	
	AC	4,405,710	09/20/83 Balasubramanyam et al. * *	430	311		
	AD	4,419,421	12/06/83 Wichelhaus et al. * *	429	191		
	AE	4,499,557	02/12/85 Holmberg et al. * *	365	163		
	AF	5,315,131	05/24/94 Kishimoto et al. * *	257	57		
	AG	5,350,484	09/27/94 Gardner et al. * *	156	628		
	AH	5,512,328	04/30/96 Yoshimura et al. * *	427	498		
	AI	5,512,773	04/30/96 Wolf et al. * *	257	471		
	AJ	5,846,889	12/08/98 Harbison et al. * *	501	40		
JMS	AK	6,117,720	09/12/00 Harshfield * *	438	238		
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
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JMS	AL	00/48196 A1	17.08.00	WIPO (Kozicki et al.) * *			
JMS	AM	02/21542 A1	14.03.02	WIPO (Kozicki et al.) * *			
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<i>JMB</i>	AA	6,143,604	11/07/00	Chiang et al. * *	438	253		
<i>JMB</i>	AB	6,177,338 B1	01/23/01	Liaw et al. * *	438	629		
<i>JMB</i>	AC	6,350,679 B1	02/26/02	McDaniel et al. * *	438	634		
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Examiner Initial	Class	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
Jms	AA	3,622,319	11/23/71	Sharp * *	96	27	
	AB	3,743,847	07/03/73	Boland * *	250	510	
	AC	4,269,935	05/26/81	Masters et al. * *	430	323	
	AD	4,312,938	01/26/82	Drexler et al. * *	430	496	
	AE	4,320,191	03/16/82	Yoshikawa et al. * *	430	296	
	AF	4,795,657	01/03/89	Formigoni et al. * *	427	96	
	AG	4,847,674	07/11/89	Silwa et al. * *	357	67	
	AH	5,177,567	01/05/93	Klersy et al. * *	257	4	
	AI	5,219,788	06/15/93	Abermathey et al. * *	437	187	
	AJ	5,726,083	03/10/98	Takaishi * *	438	210	
Jms	AK	5,751,012	05/12/98	Wolstenholme et al. * *	257	5	

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Class	Subclass	Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
Jms	AN		Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989). * *
Jms	AO		Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY pp. 24-29 (1982) * *
Jms	AP		Hilt, DISSERTATION: <i>Materials Characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. title page-114 (UMI Company, May 1999). * *

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					FILING DATE March 1, 2001		GROUP 2813	
U.S. PATENT DOCUMENTS								
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Jm ↑	AA	5,789,277	08/04/98	Zahorik et al. ✕ ✕	438	95		
	AB	5,841,150	11/24/98	Gonzalez et al. ✕ ✕	257	3		
	AC	5,920,788	07/06/99	Reinberg ✕ ✕	438	466		
	AD	5,998,066	12/07/99	Block et al. ✕ ✕	430	5		
	AE	6,077,729	06/20/00	Harshfield ✕ ✕	438	128		
	AF	6,236,059 B1	05/22/01	Wolstenholme et al. ✕ ✕	257	3		
	AG	6,297,170 B1	10/02/01	Gabriel et al. ✕ ✕	438	738		
	AH	6,300,684 B1	10/09/01	Gonzalez et al. ✕ ✕	257	774		
	AI	6,316,784 B1	11/13/01	Zahorik et al. ✕ ✕	257	3		
	AJ	6,329,606 B1	12/11/01	Freyman et al. ✕ ✕	174	260		
Jm ↓	AK	6,348,365	02/19/02	Moore et al. ✕ ✕	438	130		
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
Jm	AN	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAMIC SOC., Nos. 3-4, pp. 183-188 (Mar.-Apr. 1979). ✕ ✕						
	AO	Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983). ✕ ✕						
Jm	AP	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993). ✕ ✕						
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U.S. DEPARTMENT OF COMMERCE
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APPLICANT: John T. Moore et al.

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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
JMS	AA	6,376,284 B1	04/23/02	Gonzalez et al. * *	438	129	
	AB	6,391,688 B1	05/21/02	Gonzalez et al. * *	438	128	
	AC	6,414,376 B1	07/02/02	Thakur et al. * *	257	640	
	AD	6,418,049 B1	07/09/02	Kozicki et al. * *	365	174	
JMS	AE	6,423,628 B1	07/23/02	Li et al. * *	438	622	
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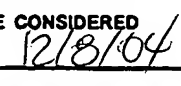
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JMS	AM		McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987). * *
JMS	AO		Miyatani, <i>Electrical Properties of Ag₂Se</i> , 13 J. Phys. Soc. Japan, p. 317 (1958). * *
JMS	AP		Mizusaki et al. <i>Kinetic Studies on the Selenization of Silver</i> , 47 BUL. CHEM. SOC. JAPAN., No. 11 pp. 2851-2855 (November 1974). * *

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JMS	AA	10/077,867		Campbell et al. (as filed) * *			02/20/2002
JMS	AB	10/232,757		Li, et al. * *			08/29/2002
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JMS	AN			Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989). * *			
JMS	AO			Safran et al., <i>TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and selenium</i> , 317 THIN SOLID FILMS, pp. 72-76 (1998). * *			
JMS	AP			Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 BUL. CHEM. SOC. JAPAN, No. 12, pp. 3662-3665 (December 1973). * *			
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	AN		Somogyi et al., Temperature Dependence of the Carrier Mobility in Ag ₂ Se Layers Grown on NaCl and SiO ₂ Substrates, 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1994). * *					
	AO		Tai et al., Multilevel Ge-Se film based resist systems, SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 32-39 (March 1982). * *					
	AP		Tai et al., Submicron optical lithography using an inorganic resist/polymer bilayer scheme, 17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept/Oct. 1980). * *					
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<i>AMW</i>	AN		West, DISSERTATION: <i>Electrically Erasable Non-Volatile Memory Via electrochemical Deposition of</i>				
			<i>Multifractal Aggregates</i> , Arizona State University, pp. title page-168 (UMI Co., May 1998). ✕✕				
<i>AMW</i>	AO		West et al., <i>Equivalent Circuit Modeling of the Ag₁As_{0.37}S_{0.37}Ag_{0.40}Ag System Prepared by</i>				
			<i>Photodissolution of Ag</i> , 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (September 1998). ✕✕				
<i>AMW</i>	AP		Yoshikawa et al., <i>A new inorganic electron resist of high contrast</i> , 31 APPL. PHYS. LETT., No. 3,				
			pp. 161-163 (August 1977). ✕ ✕				
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<div style="font-family: cursive; font-size: 1.2em;">JMS</div>	AH		Yoshikawa et al., <i>Dry development of Se-Ge Inorganic photoresist</i> , 36 APPL. PHYS. LETT., No. 1, pp. 107-109 (January 1980). ✕ ✕
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